



# PDTA143X/123J/143Z/114Y/124XQC-Q series

50 V, 100 mA PNP resistor-equipped transistors

Rev. 1 — 30 September 2021

Product data sheet

## 1. General description

100 mA PNP Resistor-Equipped Transistor (RET) family in an ultra small DFN1412D-3 (SOT8009) leadless Surface-Mounted Device (SMD) plastic package with side-wettable flanks.

Table 1. Product overview

Type number	R1	R2	Package		NPN complement:
	k $\Omega$	k $\Omega$	Nexperia	JEDEC	
PDTA143XQC-Q	4.7	10	SOT8009	MO-340CA	PDTC143XQC-Q
PDTA123JQC-Q	2.2	47			PDTC123JQC-Q
PDTA143ZQC-Q	4.7	47			PDTC143ZQC-Q
PDTA114YQC-Q	10	47			PDTC114YQC-Q
PDTA124XQC-Q	22	47			PDTC124XQC-Q

## 2. Features and benefits

- 100 mA output current capability
- Built-in resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Digital applications
- Cost saving alternative for BC857-Q series in digital applications
- Controlling IC inputs
- Switching loads

## 4. Quick reference data

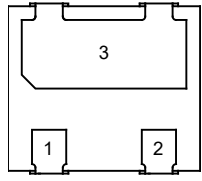
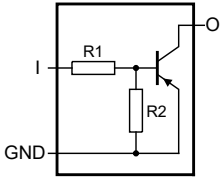
Table 2. Quick reference data

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
$I_O$	output current		-	-	-100	mA

## 5. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)	 <p>Transparent top view</p>	 <p>aaa-019606</p>
2	GND	GND (emitter)		
3	O	output (collector)		

## 6. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PDTA143XQC-Q	DFN1412D-3	plastic leadless ultra small outline package with side-wettable flanks (SWF); 3 terminals; 0.8 mm pitch; body: 1.4 x 1.2 x 0.48 mm	SOT8009
PDTA123JQC-Q			
PDTA143ZQC-Q			
PDTA114YQC-Q			
PDTA124XQC-Q			

## 7. Marking

Table 5. Marking

Type number	Marking code
PDTA143XQC-Q	8F
PDTA123JQC-Q	8C
PDTA143ZQC-Q	8G
PDTA114YQC-Q	8B
PDTA124XQC-Q	6F

## 8. Limiting values

**Table 6. Limiting values**

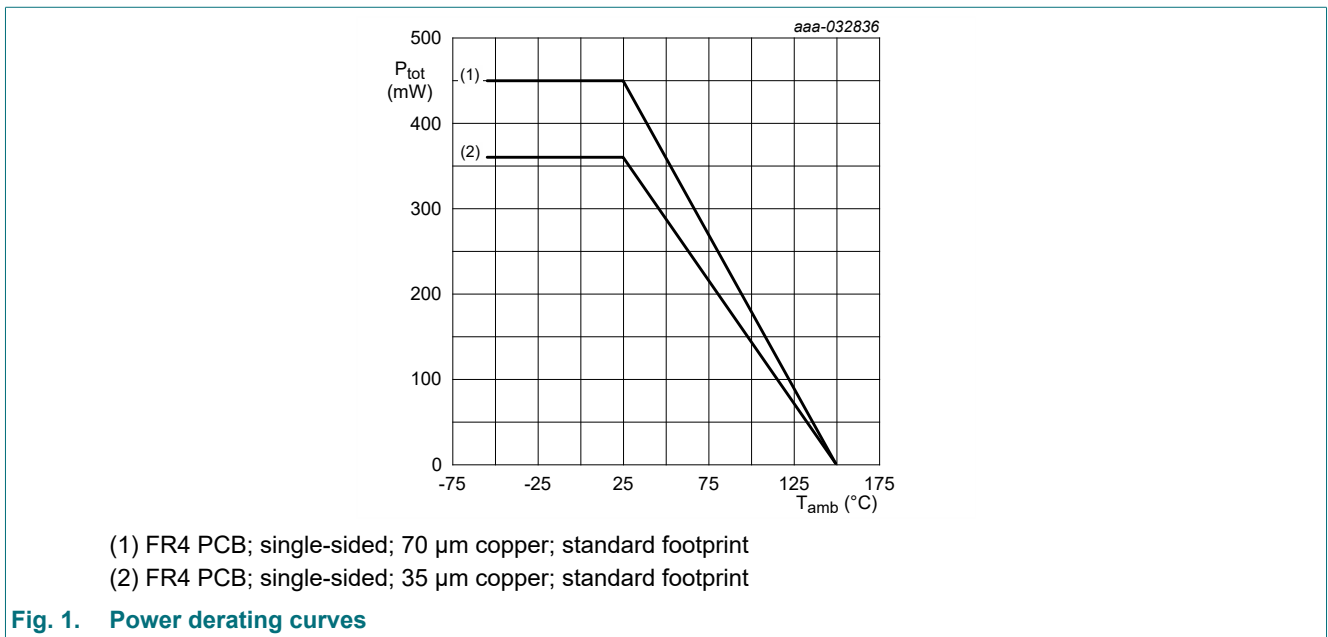
In accordance with the Absolute Maximum Rating System (IEC 60134).

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Max	Unit	
$V_{CBO}$	collector-base voltage	open emitter	-	-50	V	
$V_{CEO}$	collector-emitter voltage	open base	-	-50	V	
$V_{EBO}$	emitter-base voltage					
	PDTA143XQC-Q	open collector	-	-7	V	
	PDTA123JQC-Q		-	-5	V	
	PDTA143ZQC-Q		-	-5	V	
	PDTA114YQC-Q		-	-6	V	
	PDTA124XQC-Q		-	-7	V	
$V_i$	input voltage					
	PDTA143XQC-Q		-30	+7	V	
	PDTA123JQC-Q		-12	+5	V	
	PDTA143ZQC-Q		-30	+5	V	
	PDTA114YQC-Q		-40	+6	V	
	PDTA124XQC-Q		-40	+7	V	
$I_O$	output current		-	-100	mA	
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1]	-	360	mW
			[2]	-	450	mW
$T_j$	junction temperature		-	150	°C	
$T_{amb}$	ambient temperature		-55	150	°C	
$T_{stg}$	storage temperature		-65	150	°C	

[1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided; 35  $\mu\text{m}$  copper; tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB; single-sided; 70  $\mu\text{m}$  copper; tin-plated and standard footprint.



(1) FR4 PCB; single-sided; 70  $\mu\text{m}$  copper; standard footprint  
(2) FR4 PCB; single-sided; 35  $\mu\text{m}$  copper; standard footprint

**Fig. 1. Power derating curves**

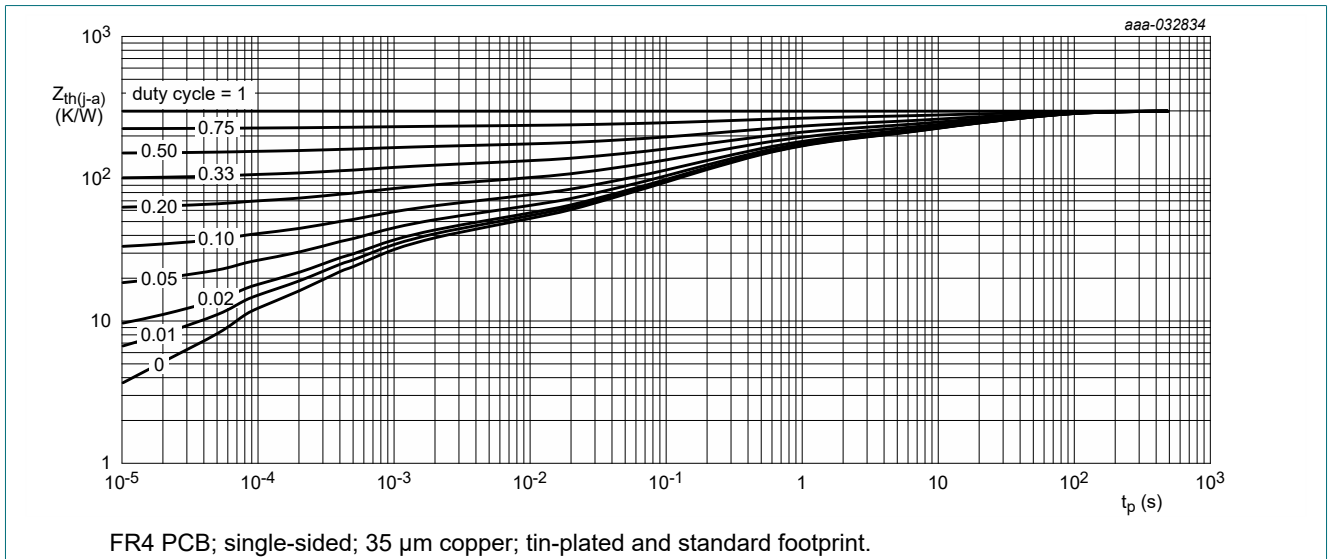
## 9. Thermal characteristics

**Table 7. Thermal characteristics**

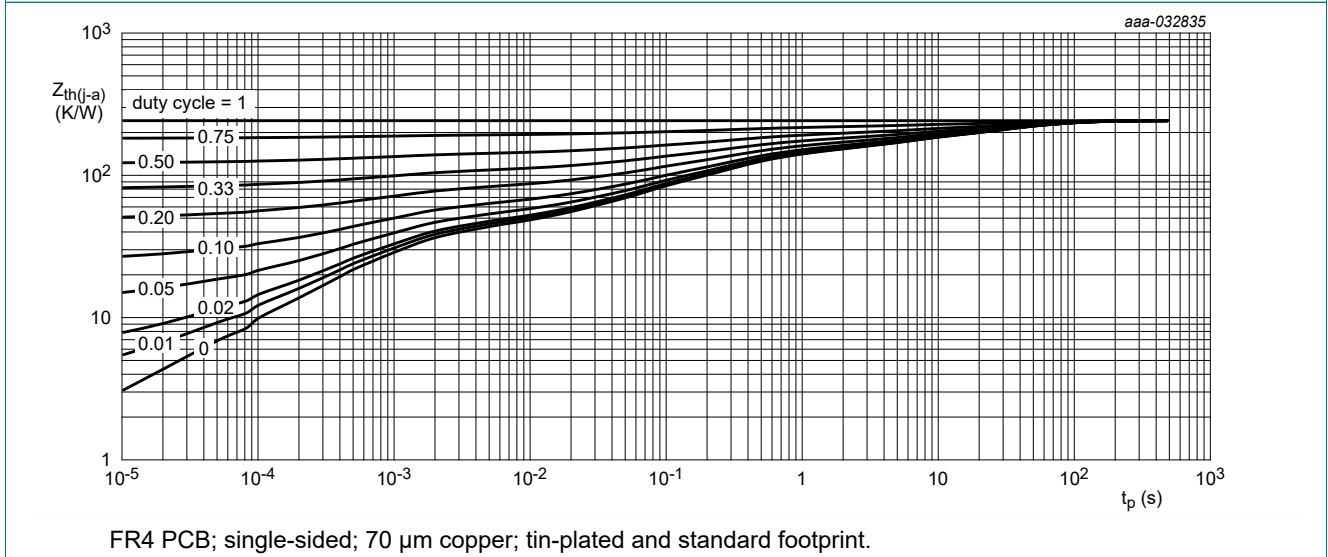
$T_{amb} = 25\text{ °C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	348	K/W
			[2]	-	-	278	K/W

- [1] Device mounted on an FR4 PCB; single-sided; 35  $\mu\text{m}$  copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided; 70  $\mu\text{m}$  copper; tin-plated and standard footprint.



**Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**



**Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values**

## 10. Characteristics

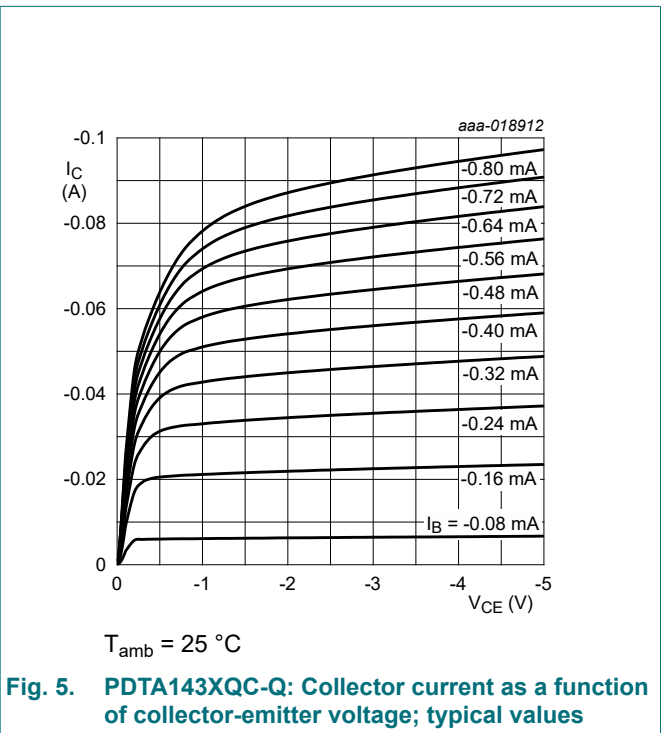
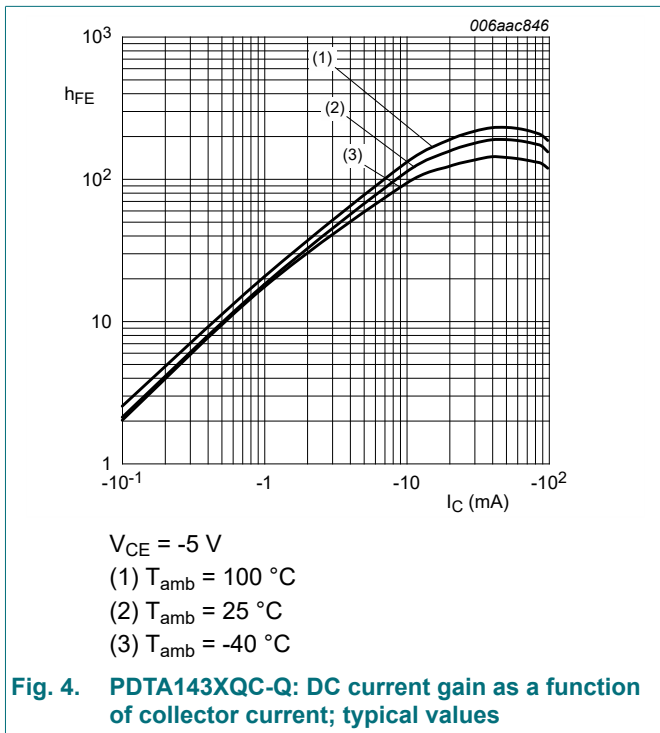
**Table 8. Characteristics**
 $T_{amb} = 25\text{ °C}$  unless otherwise specified.

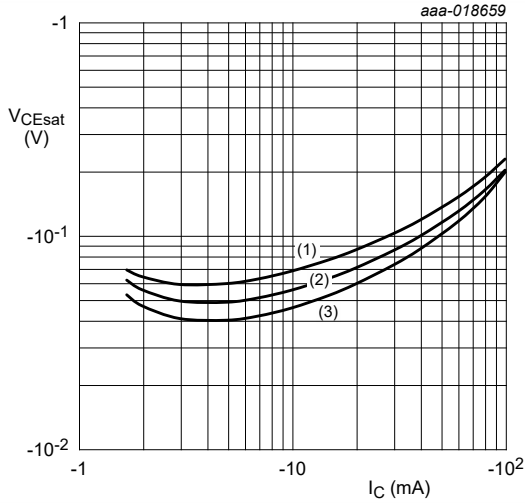
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = -100\ \mu\text{A}$ ; $I_E = 0\ \text{A}$	-50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = -2\ \text{mA}$ ; $I_B = 0\ \text{A}$	-50	-	-	V
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -50\ \text{V}$ ; $I_E = 0\ \text{A}$	-	-	-100	nA
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = -30\ \text{V}$ ; $I_B = 0\ \text{A}$	-	-	-100	nA
		$V_{CE} = -30\ \text{V}$ ; $I_B = 0\ \text{A}$ ; $T_j = 150\text{ °C}$	-	-	-5	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current					
	PDTA143XQC-Q	$V_{EB} = -5\ \text{V}$ ; $I_C = 0\ \text{A}$	-	-	-600	$\mu\text{A}$
	PDTA123JQC-Q		-	-	-180	$\mu\text{A}$
	PDTA143ZQC-Q		-	-	-170	$\mu\text{A}$
	PDTA114YQC-Q				-150	$\mu\text{A}$
	PDTA124XQC-Q				-120	$\mu\text{A}$
$h_{FE}$	DC current gain					
	PDTA143XQC-Q	$V_{CE} = -5\ \text{V}$ ; $I_C = -10\ \text{mA}$	50	-	-	
	PDTA123JQC-Q		100	-	-	
	PDTA143ZQC-Q		100	-	-	
	PDTA114YQC-Q	$V_{CE} = -5\ \text{V}$ ; $I_C = -5\ \text{mA}$	100	-	-	
	PDTA124XQC-Q		80	-	-	
$V_{CEsat}$	collector-emitter saturation voltage					
	PDTA143XQC-Q	$I_C = -10\ \text{mA}$ ; $I_B = -0.5\ \text{mA}$	-	-	-100	mV
	PDTA123JQC-Q	$I_C = -5\ \text{mA}$ ; $I_B = -0.25\ \text{mA}$	-	-	-100	mV
	PDTA143ZQC-Q		-	-	-100	mV
	PDTA114YQC-Q		-	-	-100	mV
	PDTA124XQC-Q	$I_C = -10\ \text{mA}$ ; $I_B = -0.5\ \text{mA}$	-	-	-100	mV
$V_{I(off)}$	off-state input voltage					
	PDTA143XQC-Q	$V_{CE} = -5\ \text{V}$ ; $I_C = -100\ \mu\text{A}$	-	-0.9	-0.3	V
	PDTA123JQC-Q		-	-0.6	-0.5	V
	PDTA143ZQC-Q		-	-0.6	-0.5	V
	PDTA114YQC-Q		-	-0.7	-0.5	V
	PDTA124XQC-Q		-	-0.8	-0.5	V
$V_{I(on)}$	on-state input voltage					
	PDTA143XQC-Q	$V_{CE} = -0.3\ \text{V}$ ; $I_C = -20\ \text{mA}$	-2.5	-1.5	-	V
	PDTA123JQC-Q	$V_{CE} = -0.3\ \text{V}$ ; $I_C = -5\ \text{mA}$	-1.1	-0.75	-	V
	PDTA143ZQC-Q	$V_{CE} = -0.3\ \text{V}$ ; $I_C = -5\ \text{mA}$	-1.3	-0.9	-	V
	PDTA114YQC-Q	$V_{CE} = -0.3\ \text{V}$ ; $I_C = -1\ \text{mA}$	-1.4	-0.8	-	V
	PDTA124XQC-Q	$V_{CE} = -0.3\ \text{V}$ ; $I_C = -2\ \text{mA}$	-2	-1.1	-	V

**50 V, 100 mA PNP resistor-equipped transistors**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R1	bias resistor 1 (input)					
	PDTA143XQC-Q		[1] 3.3	4.7	6.1	kΩ
	PDTA123JQC-Q		1.54	2.2	2.86	kΩ
	PDTA143ZQC-Q		3.3	4.7	6.1	kΩ
	PDTA114YQC-Q		7	10	13	kΩ
	PDTA124XQC-Q		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio					
	PDTA143XQC-Q		[1] 1.7	2.13	2.6	
	PDTA123JQC-Q		17	21	26	
	PDTA143ZQC-Q		8	10	12	
	PDTA114YQC-Q		3.7	4.7	5.7	
	PDTA124XQC-Q		1.7	2.13	2.6	
$f_T$	transition frequency	$V_{CE} = -5\text{ V}; I_C = -10\text{ mA}; f = 100\text{ MHz}$	[2] -	180	-	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	-	3	pF

- [1] See "Section 11: Test information" for resistor calculation and test conditions
- [2] Characteristics of built-in transistor

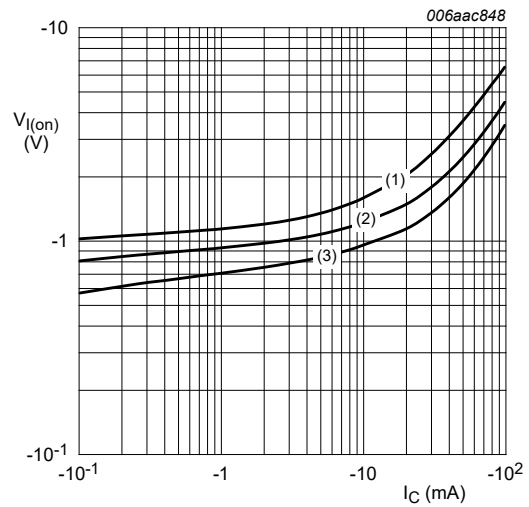




$I_C/I_B = 20$

- (1)  $T_{amb} = 100\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = -40\text{ °C}$

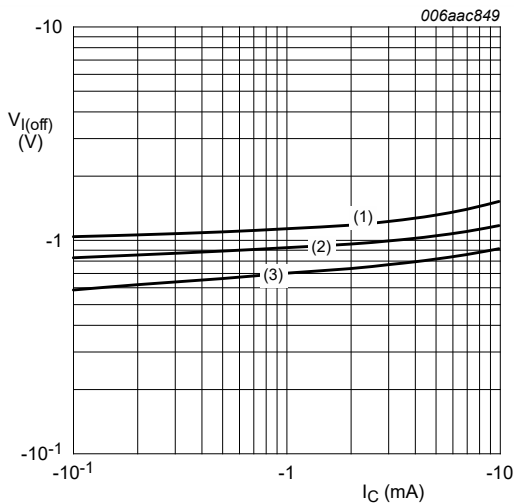
**Fig. 6. PDTA143XQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values**



$V_{CE} = -0.3\text{ V}$

- (1)  $T_{amb} = -40\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = 100\text{ °C}$

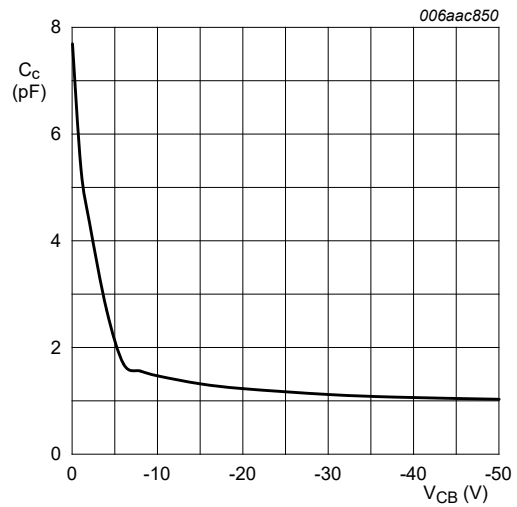
**Fig. 7. PDTA143XQC-Q: On-state input voltage as a function of collector current; typical values**



$V_{CE} = -5\text{ V}$

- (1)  $T_{amb} = -40\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = 100\text{ °C}$

**Fig. 8. PDTA143XQC-Q: Off-state input voltage as a function of collector current; typical values**



$f = 1\text{ MHz}$

$T_{amb} = 25\text{ °C}$

**Fig. 9. PDTA143XQC-Q: Collector capacitance as a function of collector-base voltage; typical values**

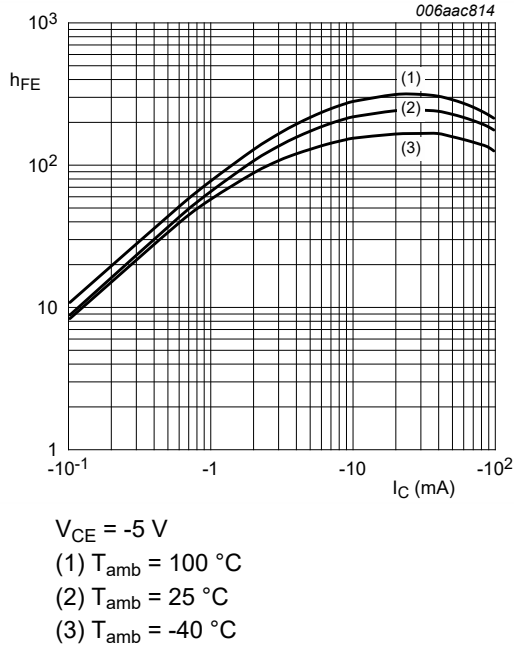


Fig. 10. PDTA123JQC-Q: DC current gain as a function of collector current; typical values

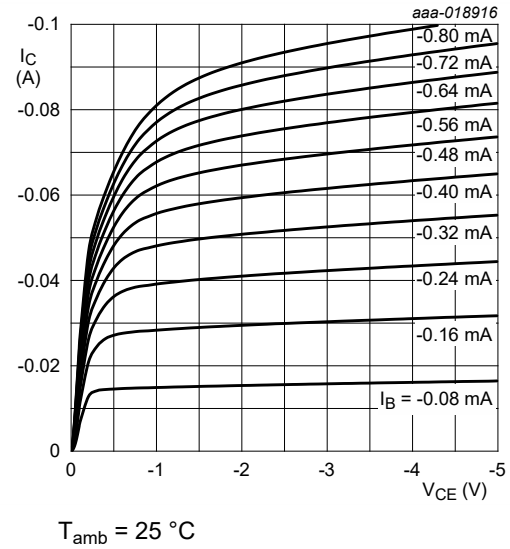


Fig. 11. PDTA123JQC-Q: Collector current as a function of collector-emitter voltage; typical values

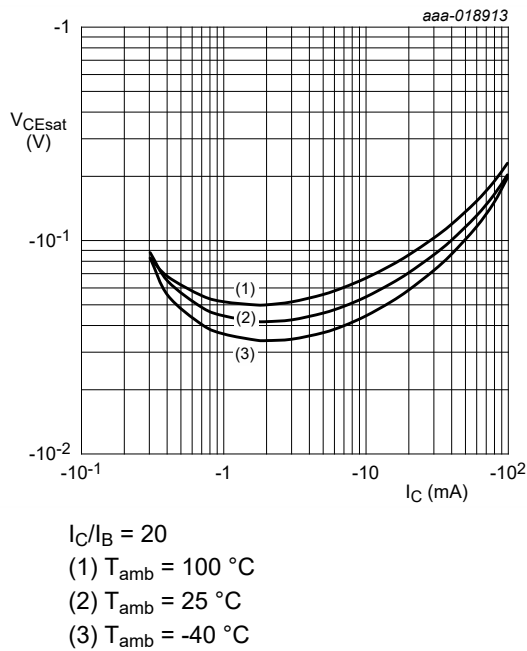


Fig. 12. PDTA123JQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values

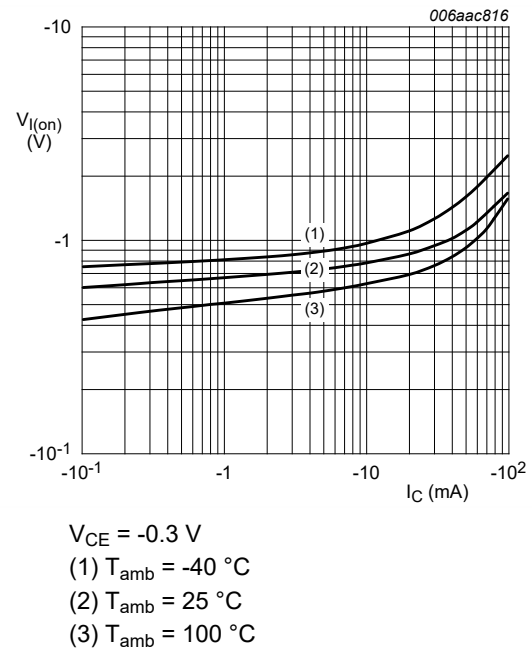
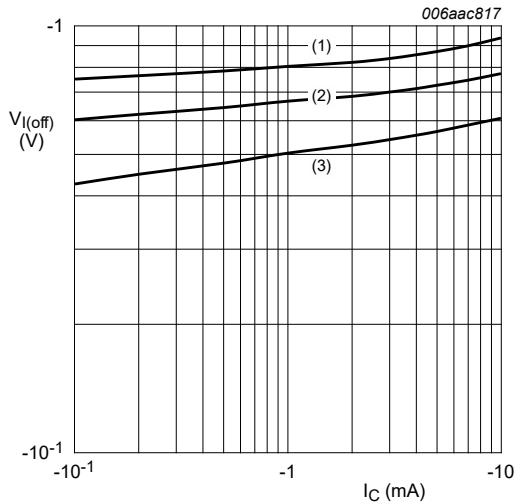


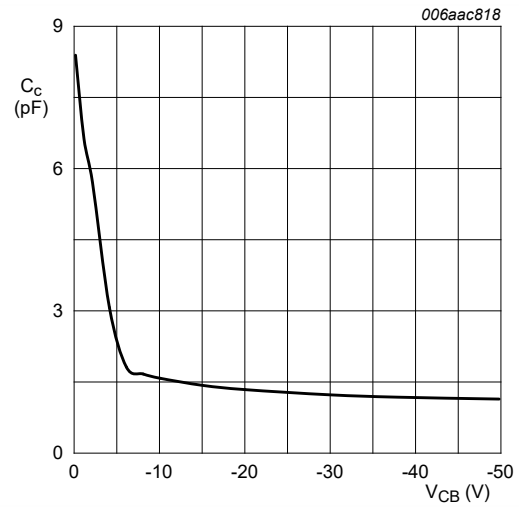
Fig. 13. PDTA123JQC-Q: On-state input voltage as a function of collector current; typical values





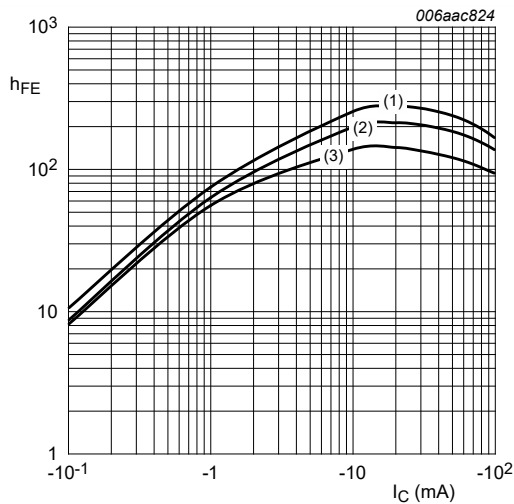
$V_{CE} = -5\text{ V}$   
 (1)  $T_{amb} = -40^\circ\text{C}$   
 (2)  $T_{amb} = 25^\circ\text{C}$   
 (3)  $T_{amb} = 100^\circ\text{C}$

Fig. 14. PDTA123JQC-Q: Off-state input voltage as a function of collector current; typical values



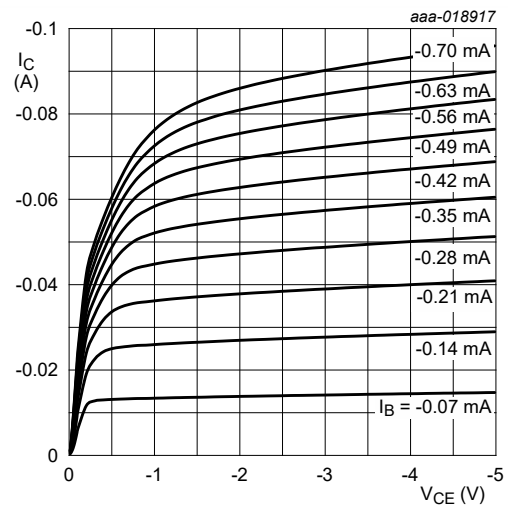
$f = 1\text{ MHz}$   
 $T_{amb} = 25^\circ\text{C}$

Fig. 15. PDTA123JQC-Q: Collector capacitance as a function of collector-base voltage; typical values



$V_{CE} = -5\text{ V}$   
 (1)  $T_{amb} = 100^\circ\text{C}$   
 (2)  $T_{amb} = 25^\circ\text{C}$   
 (3)  $T_{amb} = -40^\circ\text{C}$

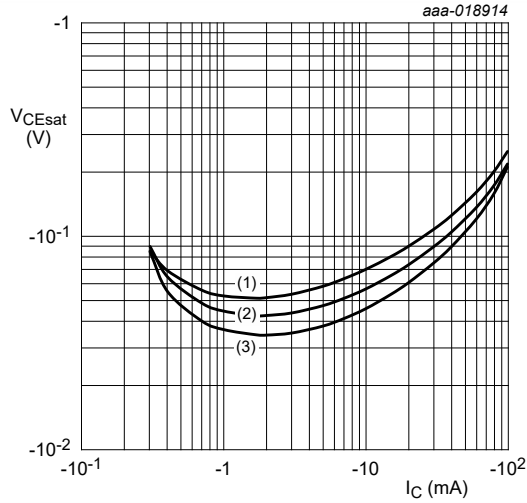
Fig. 16. PDTA143ZQC-Q: DC current gain as a function of collector current; typical values



$T_{amb} = 25^\circ\text{C}$

Fig. 17. PDTA143ZQC-Q: Collector current as a function of collector-emitter voltage; typical values

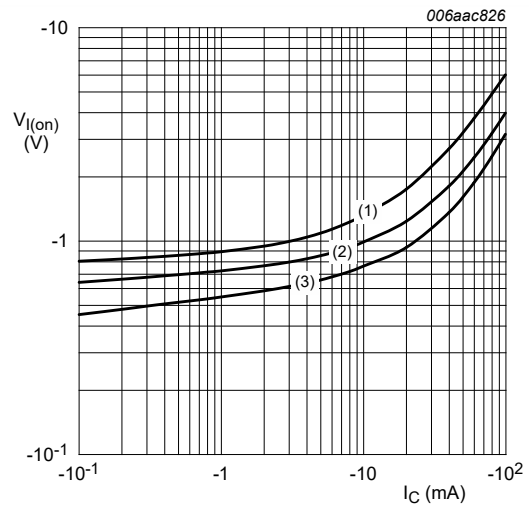
**50 V, 100 mA PNP resistor-equipped transistors**



$I_C/I_B = 20$

- (1)  $T_{amb} = 100\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = -40\text{ °C}$

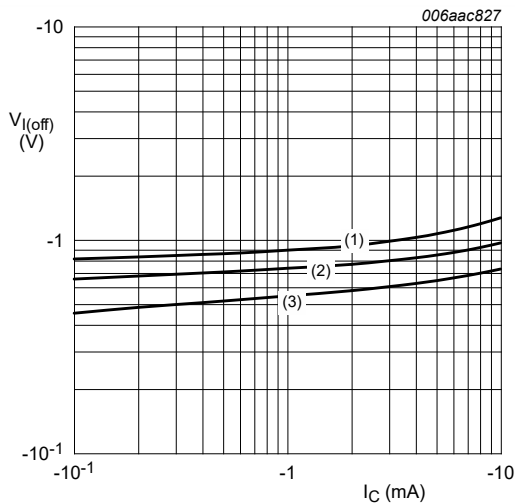
**Fig. 18. PDTA143ZQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values**



$V_{CE} = -0.3\text{ V}$

- (1)  $T_{amb} = -40\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = 100\text{ °C}$

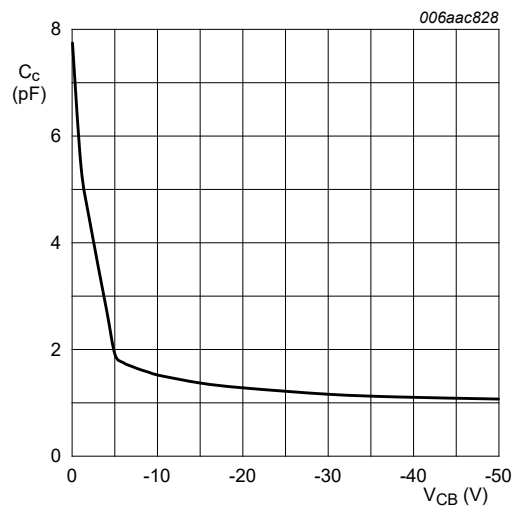
**Fig. 19. PDTA143ZQC-Q: On-state input voltage as a function of collector current; typical values**



$V_{CE} = -5\text{ V}$

- (1)  $T_{amb} = -40\text{ °C}$
- (2)  $T_{amb} = 25\text{ °C}$
- (3)  $T_{amb} = 100\text{ °C}$

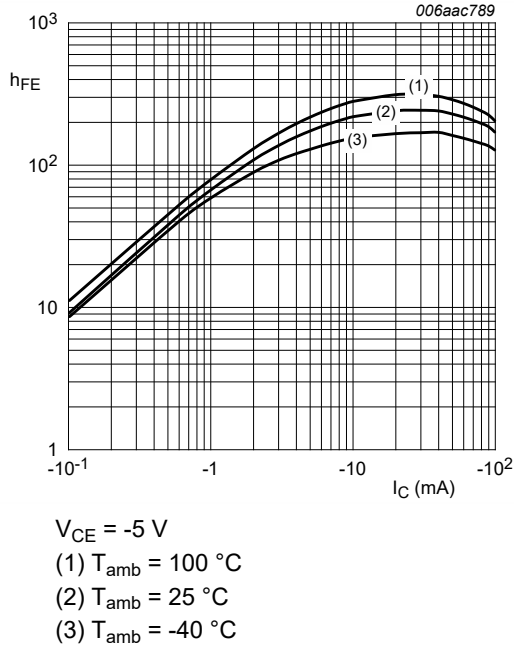
**Fig. 20. PDTA143ZQC-Q: Off-state input voltage as a function of collector current; typical values**



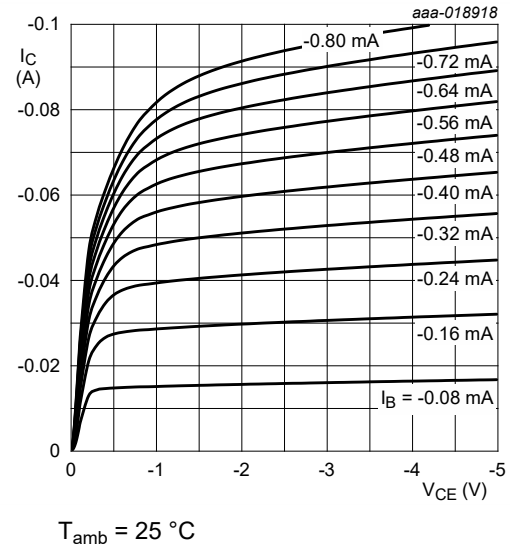
$f = 1\text{ MHz}$

$T_{amb} = 25\text{ °C}$

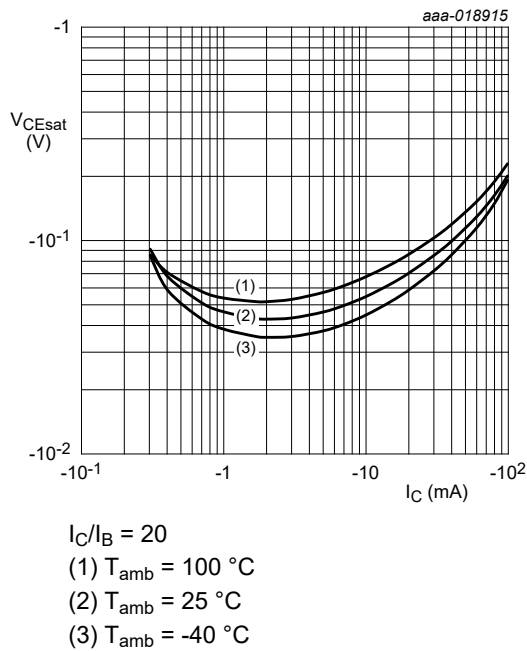
**Fig. 21. PDTA143ZQC-Q: Collector capacitance as a function of collector-base voltage; typical values**



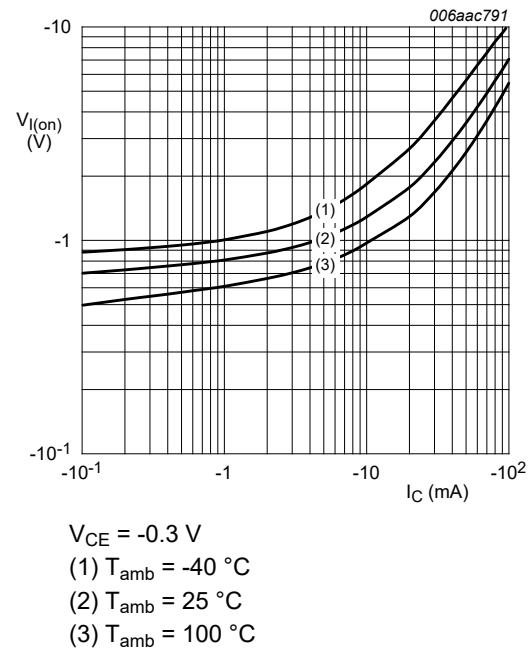
**Fig. 22. PDTA114YQC-Q: DC current gain as a function of collector current; typical values**



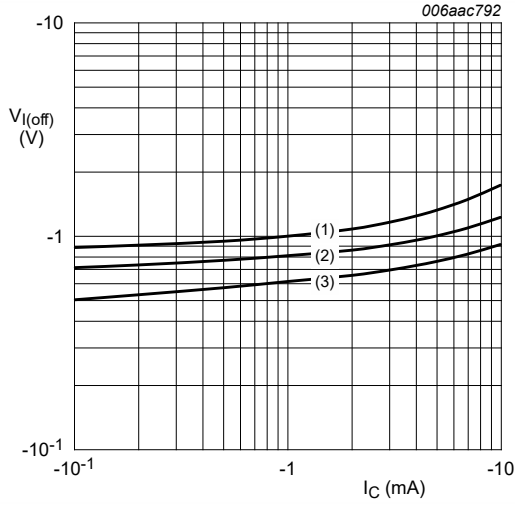
**Fig. 23. PDTA114YQC-Q: Collector current as a function of collector-emitter voltage; typical values**



**Fig. 24. PDTA114YQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values**

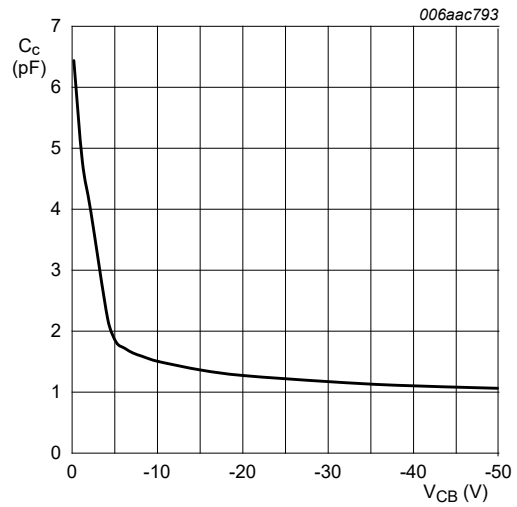


**Fig. 25. PDTA114YQC-Q: On-state input voltage as a function of collector current; typical values**



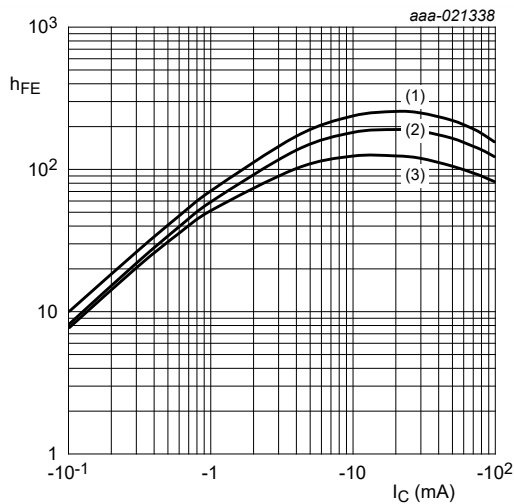
$V_{CE} = -5 \text{ V}$   
 (1)  $T_{amb} = -40 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig. 26. PDTA114YQC-Q: Off-state input voltage as a function of collector current; typical values**



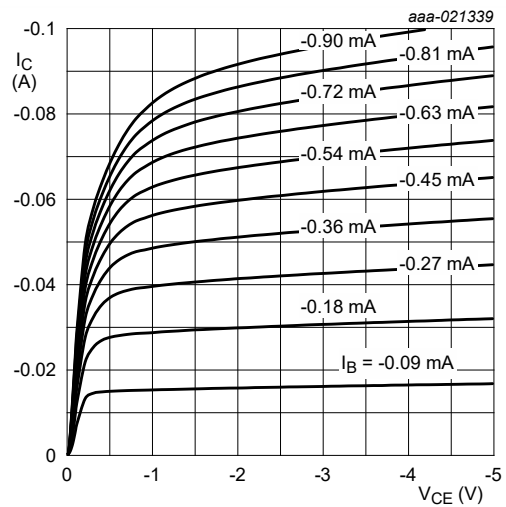
$f = 1 \text{ MHz}$   
 $T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig. 27. PDTA114YQC-Q: Collector capacitance as a function of collector-base voltage; typical values**



$V_{CE} = -5 \text{ V}$   
 (1)  $T_{amb} = 100 \text{ }^\circ\text{C}$   
 (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$   
 (3)  $T_{amb} = -40 \text{ }^\circ\text{C}$

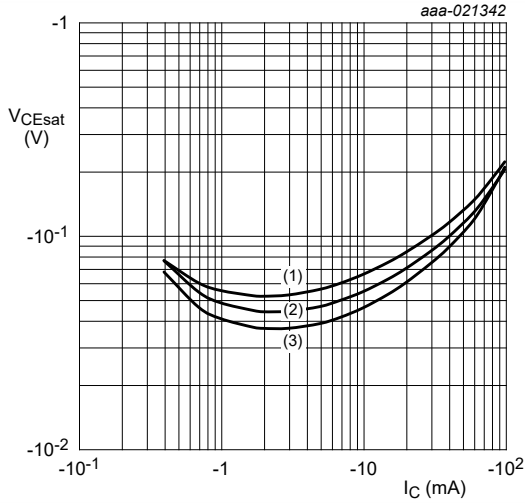
**Fig. 28. PDTA124XQC-Q: DC current gain as a function of collector current; typical values**



$T_{amb} = 25 \text{ }^\circ\text{C}$

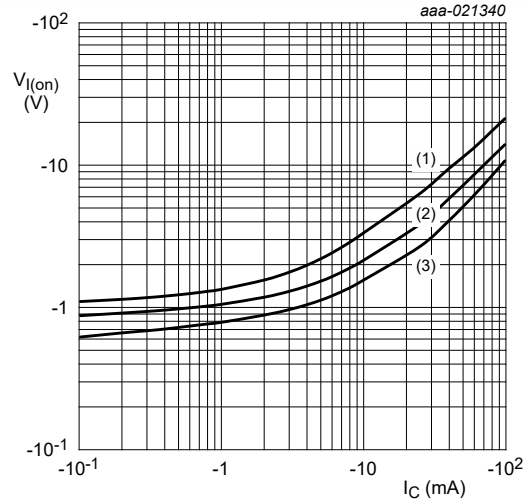
**Fig. 29. PDTA124XQC-Q: Collector current as a function of collector-emitter voltage; typical values**

50 V, 100 mA PNP resistor-equipped transistors



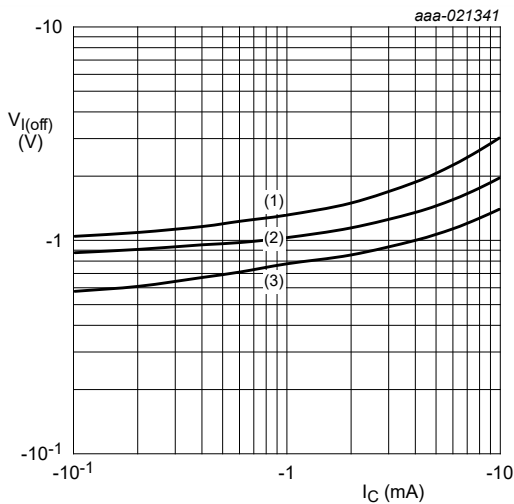
$I_C/I_B = 10$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -40\text{ °C}$

**Fig. 30. PDTA124XQC-Q: Collector-emitter saturation voltage as a function of collector current; typical values**



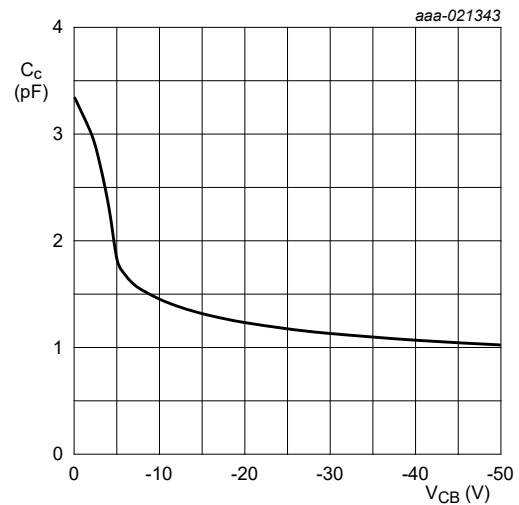
$V_{CE} = -0.3\text{ V}$   
 (1)  $T_{amb} = -40\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 100\text{ °C}$

**Fig. 31. PDTA124XQC-Q: On-state input voltage as a function of collector current; typical values**



$V_{CE} = -5\text{ V}$   
 (1)  $T_{amb} = -40\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 100\text{ °C}$

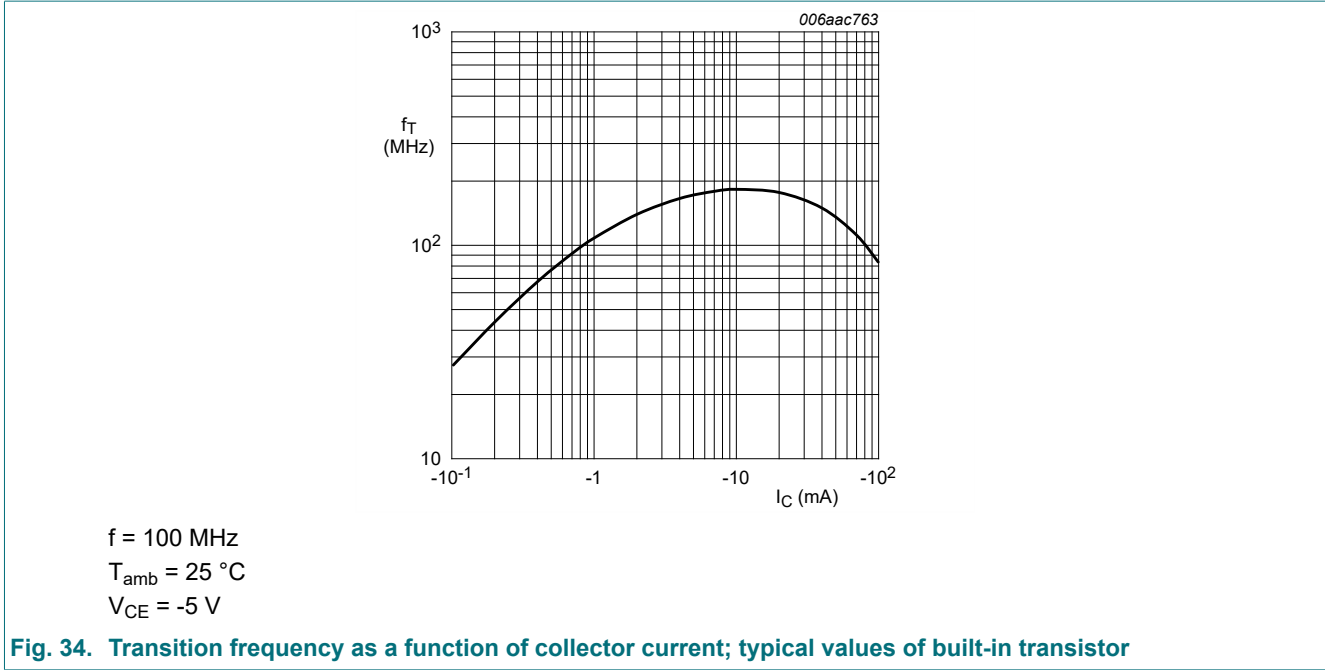
**Fig. 32. PDTA124XQC-Q: Off-state input voltage as a function of collector current; typical values**



$f = 1\text{ MHz}$   
 $T_{amb} = 25\text{ °C}$

**Fig. 33. PDTA124XQC-Q: Collector capacitance as a function of collector-base voltage; typical values**

50 V, 100 mA PNP resistor-equipped transistors



## 11. Test information

### Resistor calculation

- Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

- Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

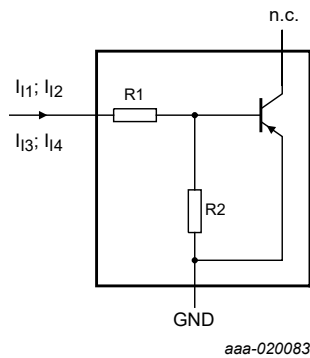


Fig. 35. PNP transistor: Resistor test circuit

### Resistor test conditions

Table 9. Resistor test conditions

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I <sub>11</sub>	I <sub>12</sub>	I <sub>13</sub>	I <sub>14</sub>
PDTA143XQC-Q	4.7	10	-350 μA	-450 μA	350 μA	450 μA
PDTA123JQC-Q	2.2	47	-90 μA	-140 μA	55 μA	105 μA
PDTA143ZQC-Q	4.7	47	-90 μA	-140 μA	55 μA	105 μA
PDTA114YQC-Q	10	47	-90 μA	-140 μA	55 μA	105 μA
PDTA124XQC-Q	22	47	-55 μA	-105 μA	55 μA	105 μA

## 12. Package outline

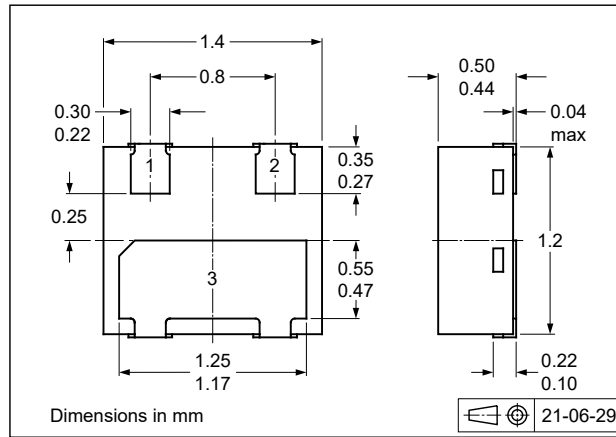
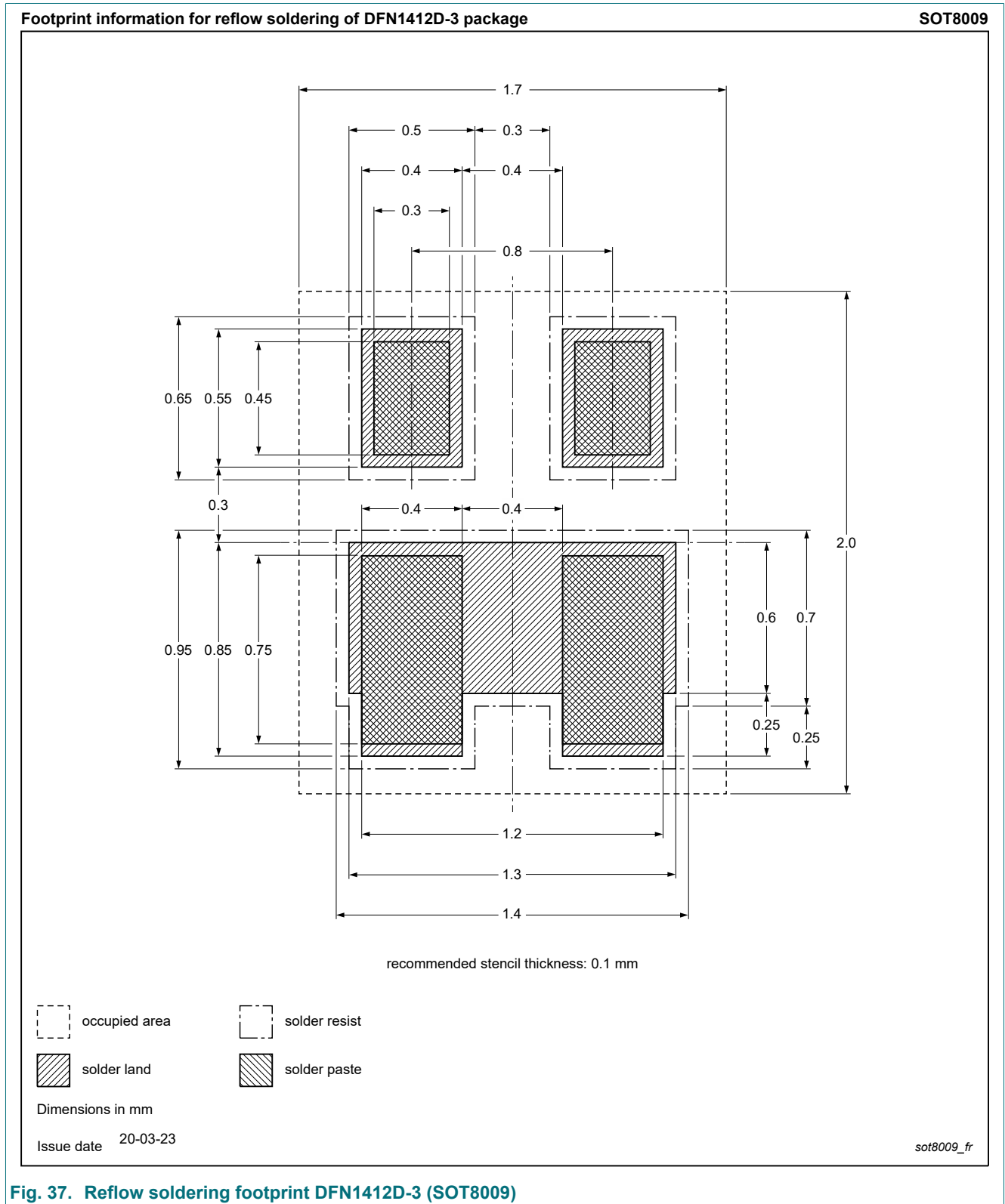


Fig. 36. Package outline DFN1412D-3 (SOT8009)



### 13. Soldering



**Fig. 37. Reflow soldering footprint DFN1412D-3 (SOT8009)**

## 14. Revision history

Table 10. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PDTA143X_TO_124XQC-Q_SER v.1	20210930	Product data sheet	-	-

**50 V, 100 mA PNP resistor-equipped transistors**

## 15. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <https://www.nexperia.com>.

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